PTO/SB/08A (08-03)

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Substitute for form 1449/PTO

Sheet 1

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## INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(Use as many sheets as necessary)

of 5

Con	mplete if Known	
Application Number	10/669,141	
Filing Date	September 23, 2003	-
First Named Inventor	Milan Kokta	
Art Unit	1775	
Examiner Name	Stephen J. Stein	
Attorney Docket Number	1035-BI4282	

			U. S. PATENT	DOCUMENTS	
Examiner Initials*	Cite No. <sup>1</sup>	Document Number  Number-Kind Code <sup>2 (F known)</sup>	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
	A A	US- 2 COS COS	10/07/100/		rigures Appear
227	AA	US- 3,625,868	12/07/1971	Grabmaier et al.	
772	AB	<sup>US-</sup> 3,736,158	05/29/1973	Cullen et al.	
555	AC	US- 3,816,906	06/18/1974	Falckenberg	
355	AD	<sup>US-</sup> 3,883,313	05/13/1975	Cullen et al.	
535	AE	<sup>US-</sup> 3,885,978	05/27/1975	Doi et al.	
535	AF	<sup>US-</sup> 3,990,902	11/09/1976	Nishizawa, et al.	
555	AG	US- 3,950,504	04/13/1976	Belding et al.	
535	АН	US- 4,370,739	01/25/1983	Wang et al.	
SSS	Al	<sup>US-</sup> 4,755,314	07/05/1988	Sakaguchi et al.	
535	AJ	<sup>US-</sup> 5,138,298	08/11/1992	Shino	
222	AK	<sup>US-</sup> 5,850,410	12/15/1998	Kuramata	
533	AL	<sup>US-</sup> 6,533,874 B1	03/18/2003	Vaudo et al.	
Sas	AM	<sup>US-</sup> 2003/0188678 A1	10/09/2003	Kokta et al.	•
535	AN	US- 6,839,362 B2	01/05/2005	Kokta et al.	
553	AO	US- 6,844,084 B2	01/18/2005	Kokta et al.	
533	AP	US- 3,424,955	01/28/1969	Seiter et al.	
275	AQ	<sup>US-</sup> 5,557,624	09/17/1996	Stultz, et al.	
222	AR	<sup>US-</sup> 6,366,596	04/02/2002	Yin, et al.	·
222	AS	<sup>US-</sup> 6,023,479	02/08/2000	Thony, et al.	

	·	FORE	IGN PATENT DOC	UMENTS		
Examiner Initiats*	Cite No.1	Foreign Patent Document	Publication Date	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines,	
_		Country Code <sup>3</sup> Number <sup>4</sup> Kind Code <sup>5</sup> (if known)	MM-OD-YYYY	Applicant of Cited Document	Where Relevant Passages Or Relevant Figures Appear	T <sup>6</sup>
207	AT	FR 1,471,976	03/24/1966	Siemens Aktiengesellsc.	Corr. 3,424,955	
223	AU	JP 11-157997	06/15/1999	Kyocera Corporation	Abstract Only	
282	AV	JP 09-278595	10/28/1997	Sumitomo Elect. Ind. Ltd.	Abstract Only	П
222	AW	JP 62-188325	08/17/1987	Sumitomo Elect. Ind. Ltd.	Abstract Only	
252	AX	JP 58-211736	12/09/1983	Toshiba Corporation	Abstract Only	
222	AY	JP 07-307316	11/21/1995	Sumitomo Elect. Ind. Ltd.	Abstract Only	

Examiner

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Substitute for form 1449/PTO	Complete if Known		
	Application Number	10/669,141	
INFORMATION DISCLOSURE	Filing Date	September 23, 2003	
	First Named Inventor	Milan R. Kokta	
STATEMENT BY APPLICANT	Art Unit	1775	
(Use as many sheets as necessary)	Examiner Name	Stephen J. Stein	
Chart 2	Attornov Docket Number	1025 DI4202	

			U. S. PATEN	T DOCUMENTS	
Examiner Initials*	Cite No.1	Document Number  Number-Kind Code <sup>2 (f known)</sup>	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
222	ВА	US- 4,963,520	10/16/1990	Yoo, et al.	riguies Appear
	<del></del>	US- 5 000 700		<del></del>	
<u>535</u>	BB	US- 5,982,796	11/09/1999	Kokta, et al.	
<u> 515</u>	ВС	US- 5,654,973	08/05/1997	Stultz, et al.	
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	BS	US-	<u> </u>		

		FORE	IGN PATENT DOCI	JMENTS		
Examiner Initials*	Cite No.	Foreign Patent Document	Publication Date	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages	Γ
		. Country Code <sup>3</sup> Number <sup>4</sup> Kind Code <sup>5</sup> (if known)	MM-DD-YYYY	Apricant of Ones Seamen	Or Relevant Figures Appear	T <sup>0</sup>
272	BT	EP 0 263 171 B1	11/25/1992	UOP		
523	BU	EP 0 762 930 B1	07/12/2000	BP Amoco Corporation		
1/	BV	WO 01/99155 A2	12/27/2001	Nichia Corporation		
	BW	WO 02/095887 A2	11/28/2002	SG Ceramics & Plastics, Inc.		
	BX					
	BY					

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Examiner Signature	Start	Sten	Date Considered	5/26/2005

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INFORMATION DISCLOSURE	Filing Date	September 23, 2003	
STATEMENT BY APPLICANT	First Named Inventor	Milan R. Kokta	
(Use as many sheets as necessary)	Art Unit	1775	
(3333311)	Examiner Name	Stephen J. Stein	
Sheet 3 of 5	Attorney Docket Number	1035-BI4282	

		NON PATENT LITERATURE DOCUMENTS	
Examiner Initials*	Cite No.1	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
SIS	CA	Efimov, A.N., et al., "On an Unusual Azimuthal Orientation Relationship in the System Gallium Nitride Layer on Spinel Substrate", CRYSTALLOGRAPHY REPORTS, 45(2): 312-317 (2000).	
535	СВ	Sun C.J., et al., "Mg-doped green light emitting diodes over cubic (1 1 1) MgAl2O4 substrate", APP. PHYS. LETT. 72(19): 2361-2363 (1998).	
227	СС	Efimov, A.N., et al., "Symmetry constraints and epitaxial growth on non-isomorphic substrate", THIN SOLID FILMS 260: 111-117 (1995).	
222	CD	George, T., et al., "Novel symmetry in the growht of gallim nitride on magnesium aluminate substrates", APPL. PHYS. LETT. 68(3): 337-339 (1996).	
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Signature Considered 3/26/2003	Examiner Signature	Steet	Sten	Date Considered	5/26/2005
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Substitu	Substitute for form 1449/PTO			Complete if Known		
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			CLOSURE	Filing Date	September 23, 2003	
STATEMENT BY APPLICANT				First Named Inventor	Milan Kokta	
(Use as many sheets as necessary)				Art Unit	1775	
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Sheet	4	of	5	Attorney Docket Number	1035-BI4282	

		NON PATENT LITERATURE DOCUMENTS	
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217	DA	Giess et al., "Growth of Single Crystal MgGa2O4 Spinel", IBM TECHNICAL DISCLOSURE BULLETIN, Vol. 15, no. 1, June 1972, pgs 151-152, XP-002315746.	
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Sheet	5	of	5	Attorney Docket Number	1035-BI4282	

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SJS	EA	Camargo, M.B., et al., "Co2+ Y3Sc2Ga3O12 (YSGG) Passive Q-Switch for Infared Erbium Lasers," submitted to LEOS in 1994.	
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222	EF	Camargo, M.B., et al., "Broad-band 1.54 um Saturable Absorber Q-switch with Co2+, " submitted to ASSL in 1995.	
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